

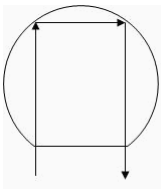
Part Number

Customer

| Category      |      | Parameter                                       | Specification                        | Measurement Method          |
|---------------|------|-------------------------------------------------|--------------------------------------|-----------------------------|
| OverallWafer  | 1.0  | Diameter                                        | 200.00 +/- 0.50 mm                   |                             |
|               | 2.0  | Notch or Flat                                   | Notched                              | Wafer Vendor                |
|               | 3.0  | Notch Direction                                 | <110> +/- 1deg                       | Wafer vendor                |
|               | 4.0  | Overall Thickness                               | 438.50 +/- 7.00 µm                   | ADE, 100%                   |
|               | 5.0  | Total Thickness Variation (TTV)                 | <5.00µm                              | Guaranteed by Process       |
|               | 6.0  | Bow                                             | <80.00µm                             | ADE to ASTM F534, 20%       |
|               | 7.0  | Warp                                            | <80.00µm                             | ADE to ASTM F657, 20%       |
|               | 8.0  | Edge Chips                                      | None                                 | Bright Light, 100% (note 2) |
|               | 9.0  | Edge Exclusion                                  | 9mm                                  |                             |
| HandleSilicon | 10.0 | Handle Growth Method                            | CZ                                   | Wafer Vendor                |
|               | 11.0 | Handle Orientation                              | {100} +/- 1.0 degree                 | Wafer Vendor                |
|               | 12.0 | Handle Thickness                                | 400.00 +/- 5.00 µm                   | ADE, 100%                   |
|               | 13.0 | Handle Doping Type                              | N                                    | Wafer Vendor                |
|               | 14.0 | Handle Dopant                                   | Phosphorous                          | Wafer Vendor                |
|               | 15.0 | Handle Resistivity                              | 0.1 - 10 Ohmcm                       | Wafer Vendor                |
|               | 16.0 | Handle Oxygen Concentration                     | < 13 ppma                            | Wafer Vendor                |
|               | 17.0 | Handle Carbon Concentration                     | < 2.5 E16 cm-3 DIN or new ASTM       | Wafer Vendor                |
|               | 18.0 | Backside Finish                                 | Polished with oxide and lasermark    |                             |
| BuriedOxide   | 19.0 | Oxide Type                                      | Thermal                              |                             |
|               | 20.0 | Oxide Thickness                                 | 10,000.00 +/- 500.00 Å               | Nanospec centre point, 4%   |
|               | 21.0 | Oxide formed on                                 | Handle and/or Device Wafer           |                             |
| DeviceSilicon | 22.0 | Device Growth Method                            | CZ                                   | Wafer Vendor                |
|               | 23.0 | Device Orientation                              | {100} +/- 1.0 degree                 | Wafer Vendor                |
|               | 24.0 | Nominal Thickness                               | 37.50 +/- 1.00 µm                    | FTIR, 100% 9-Pt (note 3)    |
|               | 25.0 | Distance to device silicon edge from wafer edge | < 2.0 mm. No Edge Grind into handle. | Typical by process          |
|               | 26.0 | Device Doping Type                              | P                                    | Wafer Vendor                |
|               | 27.0 | Device Dopant                                   | Boron                                | Wafer Vendor                |
|               | 28.0 | Device Resistivity                              | 0.01- 0.025 Ohmcm                    | Wafer Vendor                |
|               | 29.0 | Oxygen Concentration                            | < 13 ppma                            | Wafer vendor                |
|               | 30.0 | Carbon Concentration                            | < 2.5 E16 cm-3 DIN or new ASTM       | Wafer vendor                |
|               | 31.0 | Voids                                           | 0                                    | Bright Light, 100% (note 2) |
|               | 32.0 | Scratches                                       | < 25mm total length                  | Bright Light, 100% (note 2) |
|               | 33.0 | Haze                                            | none                                 | Bright Light, 100% (note 2) |

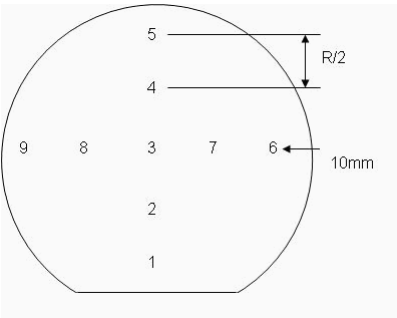
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|                   |                                                                                  |                                                                                         |                                                                                     |
|-------------------|----------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| Shipping Details  | Wafer per box :                                                                  | Max 25                                                                                  |  |
|                   | Packaging :                                                                      | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 200.00mm<br>Antistatic Double Bagging |                                                                                     |
|                   | Lot Shipment Data                                                                | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness                         |                                                                                     |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. |                                                                                         |                                                                                     |

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information